

# EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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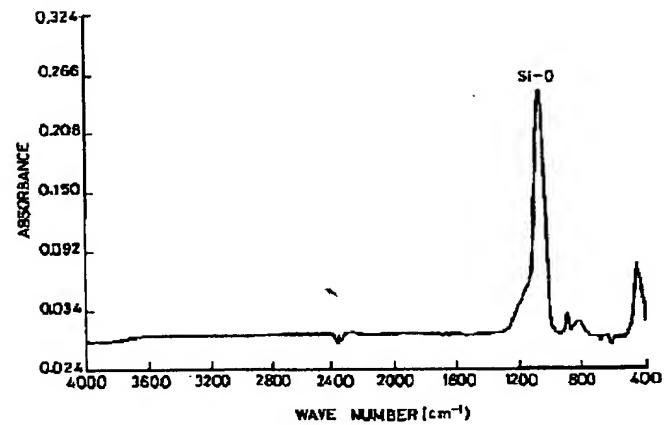
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APPLICANT : KAWASAKI STEEL CORP;

INVENTOR : MITOMO TORU;

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TITLE : METHOD FOR FORMING  
SEMICONDUCTOR FILM



ABSTRACT : PURPOSE: To provide a method for forming a semiconductor film, wherein an oxide film having a good flatness and a good film quality can be formed even on a surface of a high aspect ratio.

CONSTITUTION: A method for forming a semiconductor film, wherein a silicon oxide film is formed by a chemical vapor growth method through using as its raw material gas the gas obtained by adding a compound containing oxygen to the organic silane compound specified by a general chemical formula  $(R_1 R_2 N)_n SiH_{4-n}$  (in the formula, each of  $R_1$ ,  $R_2$  is one of  $H$ -,  $CH_3$ -,  $C_2H_5$ -,  $C_3H_7$ -,  $C_4H_9$ -, and at least one of  $R_1$ ,  $R_2$  is not  $H$ -, and  $n$  is one of integers 1-4.).

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